

/ Descriptions

WR0<5 M M E SQS æ M ç s ll 1 Silicon PNP transistor in a TO-92 Plastic Package.

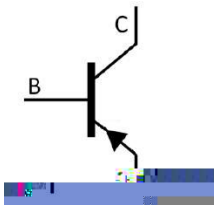
/ Features

æ ç ð ll ' ll ð ll ð ç ð ll æ "Q I ' ' High P_C and I_C .

/ Applications

æ ç æ A I ' æ ç Medium power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Collector PIN 2 χ Base PIN 3 χ Emitter

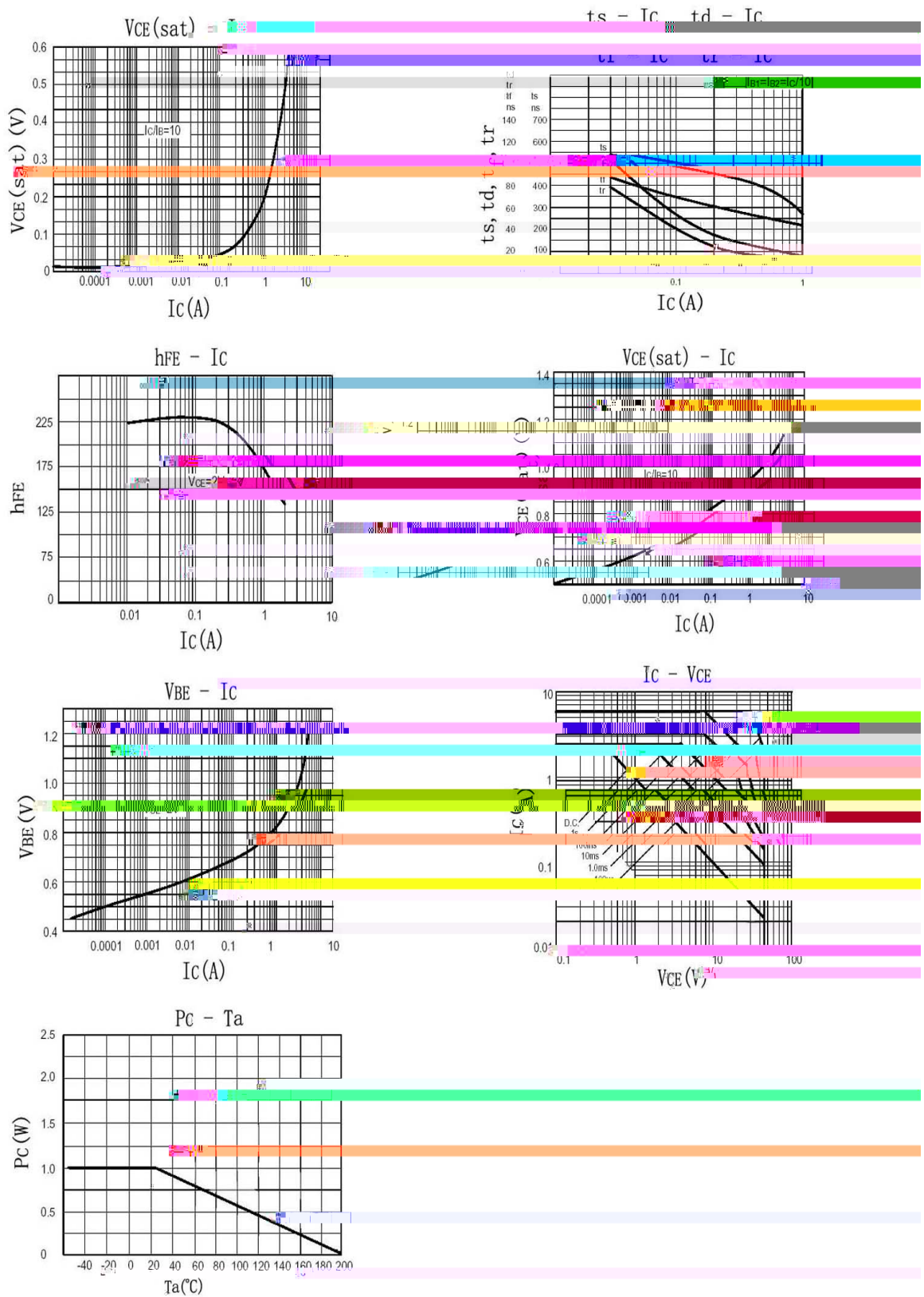
/ hFE Classifications & Marking

ø M ç ç " See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Peak Collector Current- Continuous	I_{CM}	-6.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$	-60			V
Collector to Emitter Breakdown Voltage	V	$I = -10mA$	-45			V

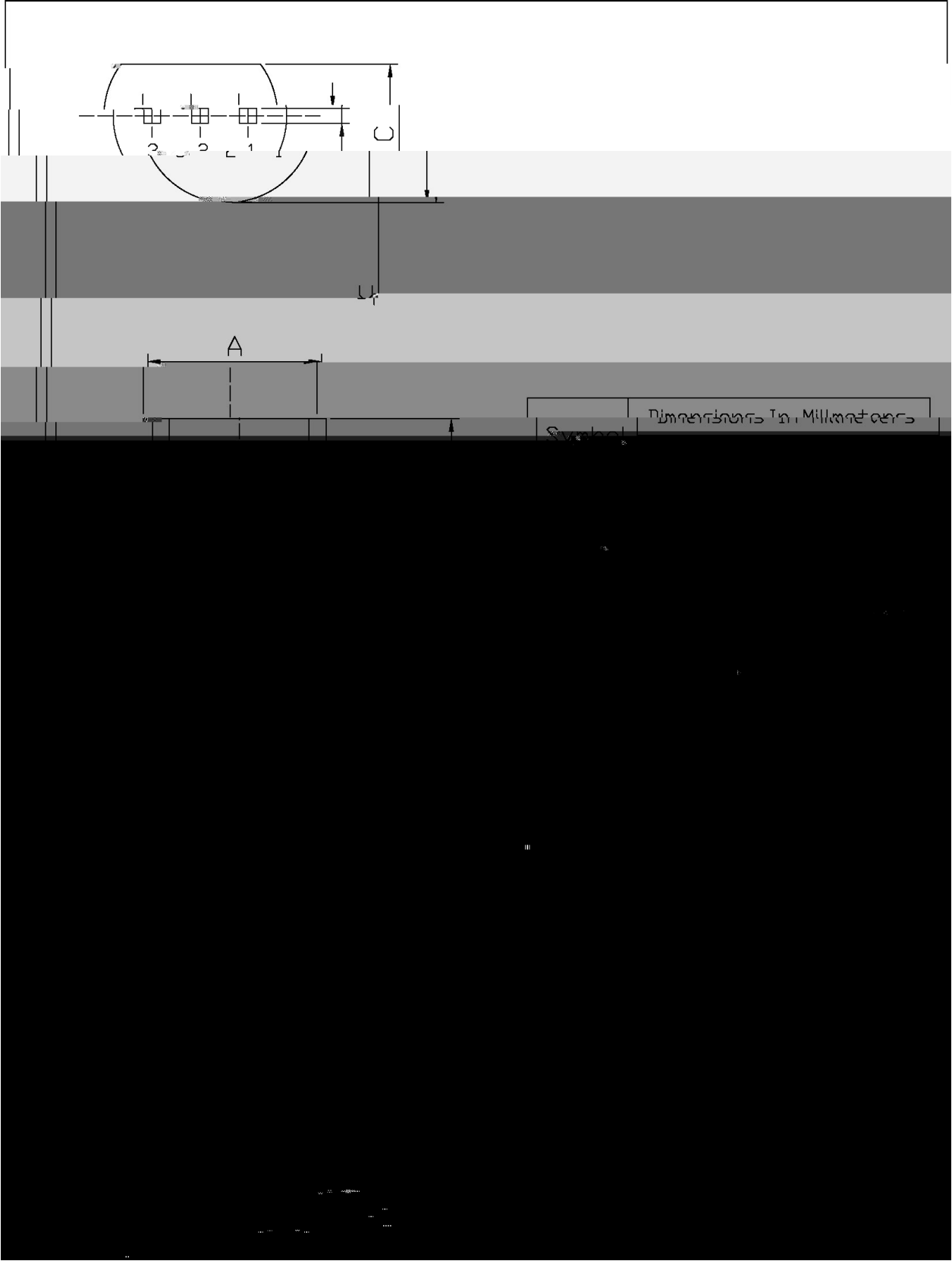
/ Electrical Characteristic Curve



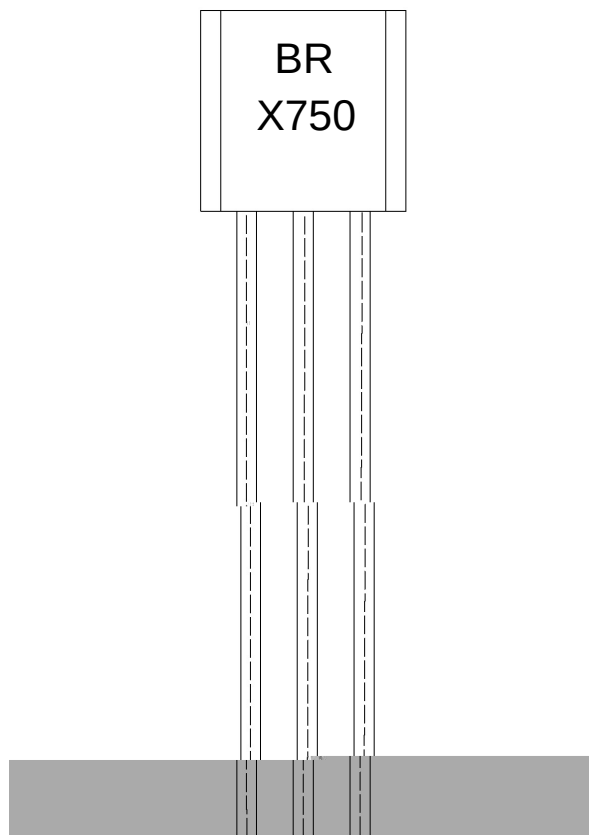
/ Package Dimensions

TO-92

Unit: mm



/ Marking Instructions



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EU:

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Note:

BR:

Company Code.

X750:

Product Type.

****:

Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. Preheating: 25~150 °C, Time: 60~90sec;
2. 2. Peak Temp.: 255 °C, Duration: 5 ° 0.5sec;
3. 3. Cooling Speed: 2~10 ° /sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255 °C, Duration: 5 ° 0.5sec.
3. Cooling Speed: 2~10 ° /sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 ± 5 °C 10 ± 1 sec. Temp: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

“Q” T Y E / BULK

Package Type	Units					Dimension		(unit mm3)

“A” V Y E / AMMO

Package Type	Units	Dimension	(unit mm3)
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